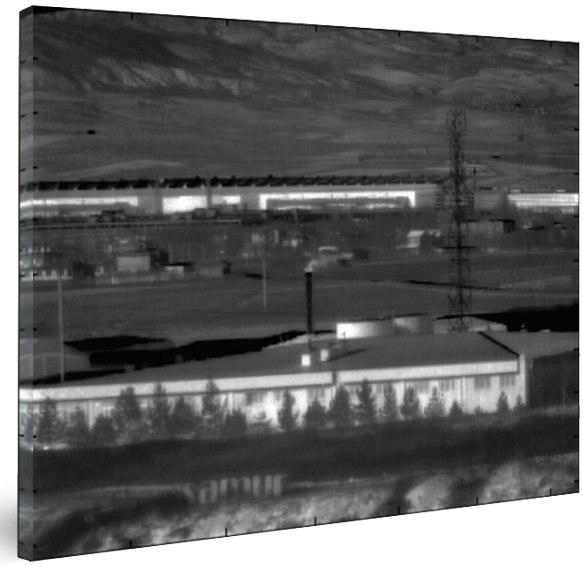
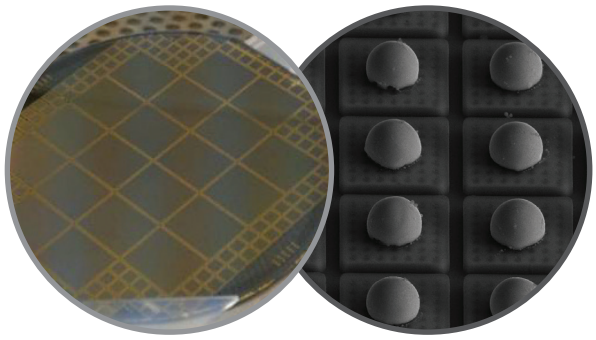
aselsan

HIGH SPEED QWIP 640

HIGH QUANTUM AND CONVERSION EFFICIENCY

BIAS ADJUSTABLE PHOTOCONDUCTIVE GAIN IN A WIDE RANGE FOR DIFFERENT OPERATION CONDITIONS





HIGH SPEED QWIP 640

FPA Specifications

Dual Band QWIP 640 IDDCA can be adapted to high resolution thermal imaging for all military and civilian applications.

Array type
640x512 InP/InGaAs QWIP

Pixel pitch
20 µm or 25 µm

Spectral response
$\lambda_c \geq 9$ µm, $\Delta\lambda \geq 1$ µm

FPA operating temperature
Up to 77 K

Operation modes
Snapshot

Charge capacity
11 Me^-

Number of outputs
1, 2 or 4

Max. frame rate
100 Hz (4 output)

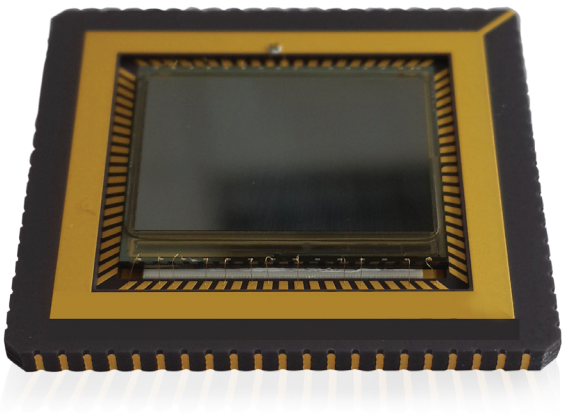
NETD
≤25 mK (τ=3 ms, f/2, T=70 K)
≤40 mK (τ=500 µs, f/2, T=70 K)
≤40 mK (τ=5 ms, f/2, T=77 K)

Operability
> 99.5%

Conversion efficiency
Adjustable up to 15%

Peak responsivity
Adjustable up to 1.0 A/W

Cooler Type
Will be determined upon customer requirements



MGEO-HSQWIP640/i001/03-2017

Developed by Quantum Devices & Nanophotonics Research Group, Middle East Technical University.

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